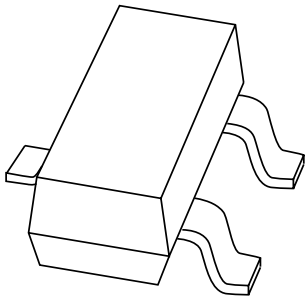
DATA SHEET



BAV199
Low-leakage double diode

Product data sheet
Supersedes data of 1999 May 11

2001 Oct 12

Low-leakage double diode BAV199

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

- Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are connected in series.

MARKING

TYPE NUMBER	MARKING CODE(1)
BAV199	JY∗

Note

1. ∗ = p: Made in Hong Kong.
   ∗ = t: Made in Malaysia.
   ∗ = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	anode; cathode

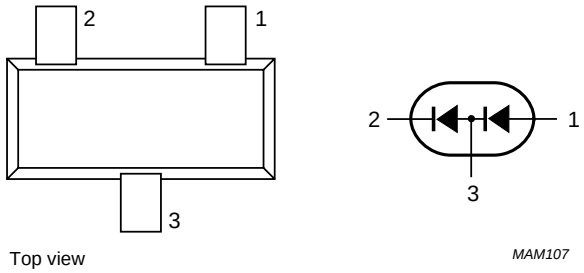


Fig.1 Simplified outline (SOT23) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; note 1; see Fig.2	–	160	mA
		double diode loaded; note 1; see Fig.2	–	140	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t_p = 1 μs	–	4	A
		t_p = 1 ms	–	1	A
		t_p = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on a FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	900	mV
		I_F = 10 mA	–	1000	mV
		I_F = 50 mA	–	1100	mV
		I_F = 150 mA	–	1250	mV
I_R	reverse current	see Fig.5			
		V_R = 75 V	0.003	5	nA
		V_R = 75 V; T_j = 150 °C	3	80	nA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	0.8	3	μs

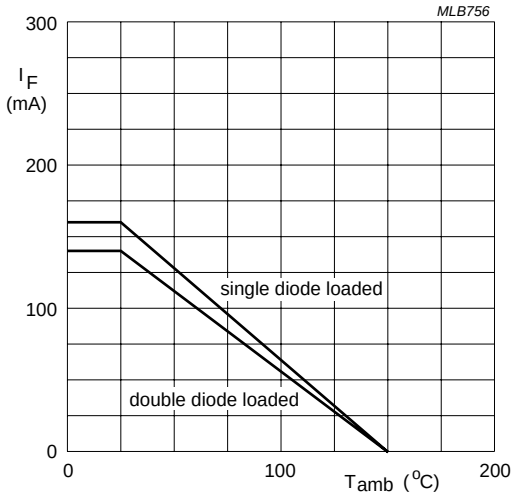
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

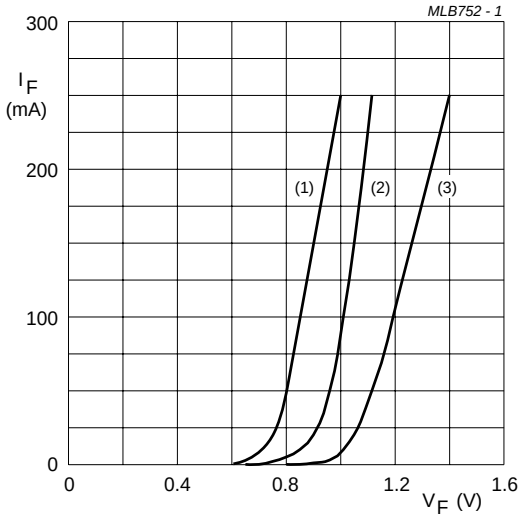
1. Device mounted on a FR4 printed-circuit board.

GRAPHICAL DATA



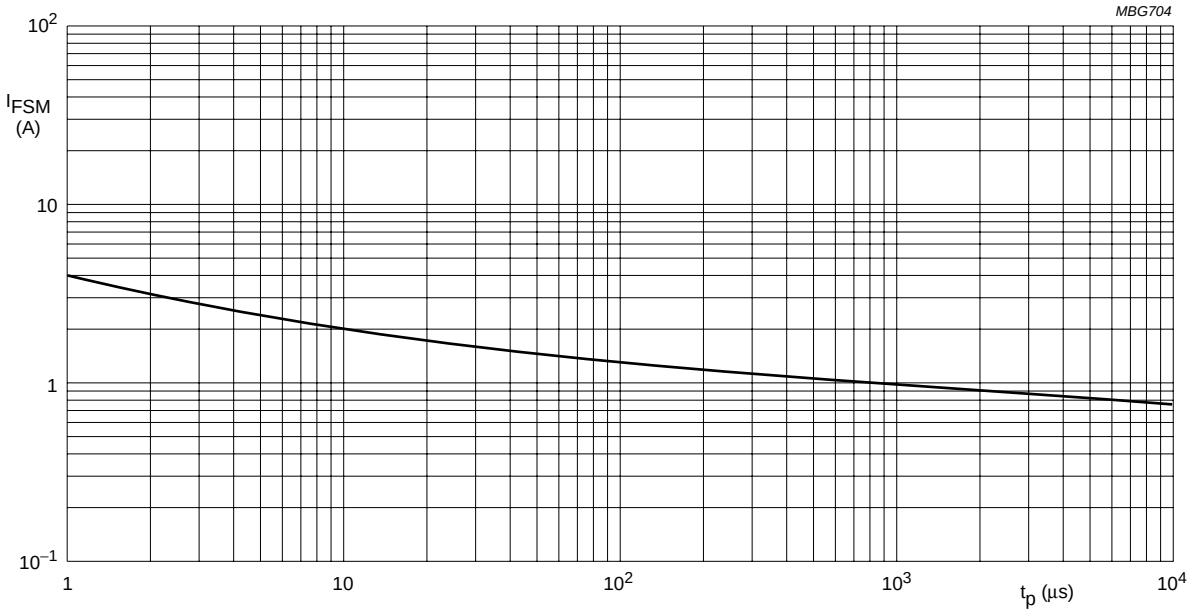
Device mounted on a FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



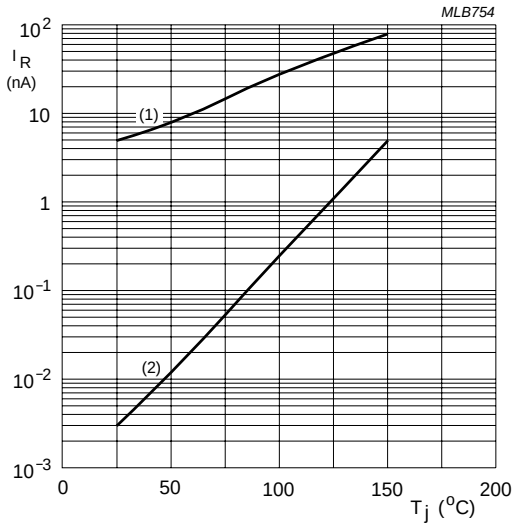
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.



Based on square wave currents; T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

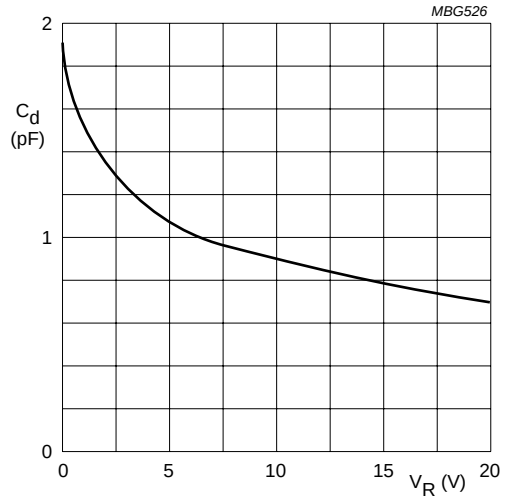


V_R = 75 V.

(1) Maximum values.

(2) Typical values.

Fig.5 Reverse current as a function of junction temperature; per diode.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.

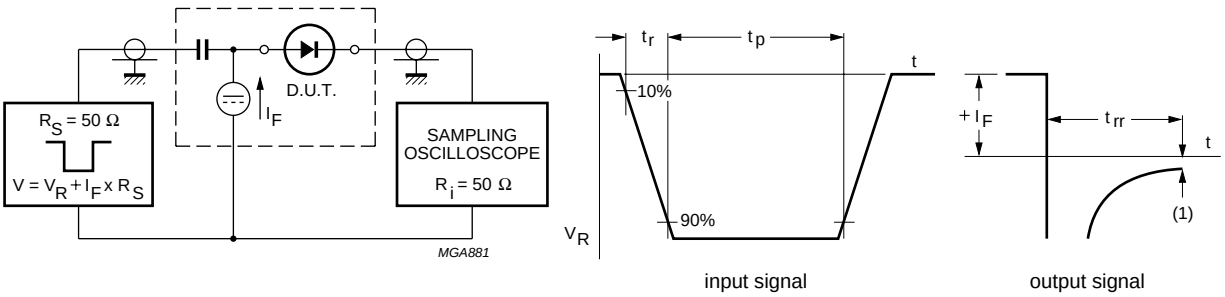
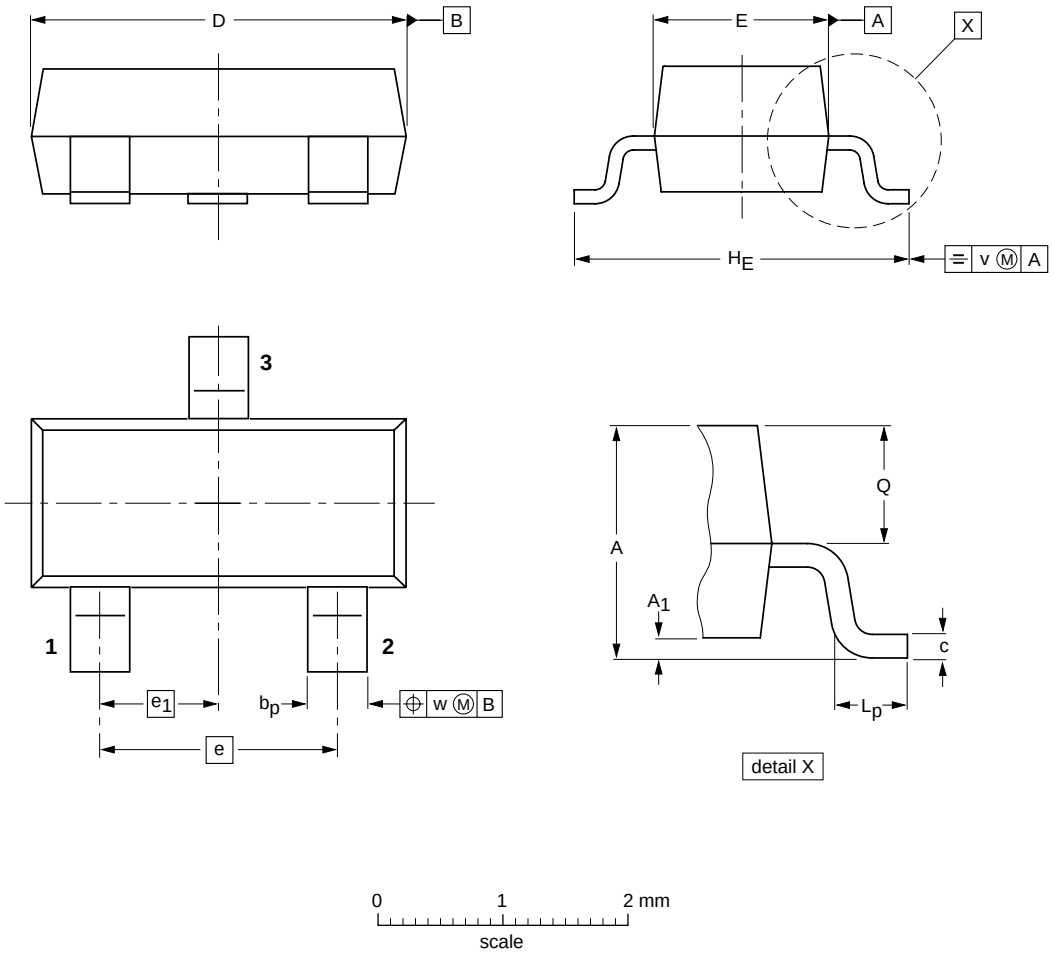


Fig.7 Reverse recovery time test circuit and waveforms.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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